

WET CLEANS FOR COBALT DISILICIDE PROCESSING

Abstract of the Disclosure

Sub 1.2 >

A method for removing a formation of oxide of titanium that is generated as a byproduct of a process that forms cobalt disilicide within an insulated-gate field effect transistor (FET).

5 The method applies a chemical reagent to the FET at a predetermined temperature, and for a predetermined period of time, necessary for removing the formation, wherein the reagent does not chemically react with the cobalt disilicide. A reagent that accomplishes this task comprises water (H_2O), ammonium hydroxide (NH_4OH), and hydrogen peroxide (H_2O_2), wherein the NH_4OH and the H_2O_2 each comprise approximately 4% of the total reagent volume. An effective
10 temperature is 65 °C combined with a 3 minute period of application.